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Past EuMIC YEP Winners

2025 Utrecht, J. Xu: An Ultra-Compact Ku-Band Doherty Power Amplifier with a Single-Footprint Triple Two-Turn Asymmetric Combiner for 6G FR3
J. Xu, E. Liu, M. Eleraky, T.-Y. Huang, C. Chu, H. Wang
2025 Utrecht, P. Umbach: Resistive D-Band Mixers with Monolithic Integrated Broadband IF Balun and LO Amplifier
P. Umbach, F. Thome, A. Leuther, R. Quay

2024 Paris, M. Wittlinger: A Frequency-Agile Digital-to-RF Power Amplifier in 22 nm FD-SOI CMOS Technology
M. Wittlinger, M. Grözing, M. Berroth, G. Rademacher

2024 Paris, G. Kaval: A 100-114 GHz GaAs MMIC Power Amplifier with Fully Integrated Dynamic Gate Bias Control for Linearization and Efficiency Enhancement
G. Kaval, G. Lasser, M. Gavell, C. Fager

2023 Berlin, A. Elmenshawi: A 75-140 GHz Frequency Quadrupler with Milli-Watt Level Output Power in 22nm FDSOI
A. Elmenshawi, M.W. Mansha, S. Muralidharan, M.M. Hella

2022 Milan, A. Engelmann: Design of Two Low DC-Power High-Efficiency D-Band Power Amplifiers in 22nm FDSOI
A. Engelmann, P. Hetterle, F. Probst, R. Weigel, M. Dietz

2021 London, T. Braun: A low Phase Noise Phase-Locked Loop with Short Settling Times for Automotive Radar
T. Braun, M. van Delden, C. Bredendiek, J. Schoepfel, N. Pohl

2020 Utrecht, T. Singh: Reconfigurable PCM GeTe-Based Latching 6-Bit Digital Switched Capacitor Bank
T. Singh, R.R. Mansour

2019 Paris, L. Nyssens: Effective Resistivity Extraction of Low-Loss Silicon Substrate at Millimeter-Wave Frequencies
L. Nyssens, M. Rack, J.-P. Raskin

2018 Madrid, A. Piacibello: Design of an S-Band Chireix Outphasing Power Amplifier Based on a Systematic Bandwidth Limitation Analysis
A. Piacibello, R. Quaglia, M. Pirola, and S.C. Cripps

2017 Nuremberg, G.P. Gibiino: Global Modeling of GaN HEMT Resistive Current Including Charge Trapping and Self-Heating for Multi-Bias Multi-Class PA Performance Prediction
G.P Gibiino, R. Cinani, A. Santarelli, F. Filicori

2016 London, A.B. Amado Rey: A 280 GHz Stacked-FET Power Amplifier Cell using 50 nm Metamorphic HEMT Technology
A.B Amado Rey, Y. Campos Roca, C. Friesicke, A. Tessmann, R. Lozar, W. Wagner, A. Leuther, M. Schlechtweg, O. Ambacher

2015 Paris, X. Yang: A novel W-Band Bottom-LO-Configured Sub-Harmonic Mixer IC in 130-nm SiGe BiCMOS
X. Yang, X. Xu, Z. Sun, T. Shibata, T. Yoshimasu

2014 Rome, C. Tzschoppe: A 2.4 GHZ Fast Switchable LNA with Transformer Matching for Wireless Wake-Up Receivers
C. Tzschoppe, R. Kostack, J. Wagner, R. Paulo, F. Ellinger

2013 Nuremberg, S. Yuan: A SiGe:C BiCMOS 140GHz Wideband Frequency Multiplier-by-8 with Differential Output
S. Yuan, H. Schumacher

2012 Amsterdam, S. Colangeli: Automated Determination of Device Noise Parameters Using Multi-Frequency, Source-Pull Data
S. Colangeli, W. Ciccognani, M. Palomba, E. Limiti

2011 Manchester, W. McGenn: RF Waveform Investigation of VSWR Sweeps on GaN HFETs
W. McGenn, J. Benedikt, P. J. Tasker, J. Powell, M. Uren

2010 Paris, P. Triverio: Extraction of Parametric Circuit Models from Scattering Parameters of Passive RF Components
P. Triverio, M. Nakhla, S. Grivet-Talocia

2009 Rome, G. Callet: A New Nonlinear HEMT Model for AlGaN/GaN Switch Applications

O. Jardel, G. Callet, C. Charbonniaud, J.C. Jacquet, N. Sarazin, E. Morvan, R. Aubry, M.-A. di Forte-Poisson, J.-P. Teyssier, S. Piotrowicz, R. Quéré

2008 Amsterdam, H. Takahashi: 120-GHz-Band Low-Noise Amplifier with 14-ps Group-Delay Variation for 10-Gbit/s Data Transmission
H. Takahashi, T. Kosugi, A. Hirata, K. Murata, N. Kukutsu

2007 Munich, M. Bao: An Active Mixer Topology for High Linearity and High Frequency Applications
M. Bao and Y. Li

2006 Manchester, G. Posada: Ar Implantation, a Passivation Technique for High-Resistivity Silicon within the MCM-D Technology
G. Posada, G. Carchon, P. Soussan, et al.